Power MOSFET

-20 V, -5.0 A, μCool™ Single P-Channel, ESD, 1.6x1.6x0.55 mm UDFN Package

Features

- UDFN Package with Exposed Drain Pads for Excellent Thermal Conduction
- Low Profile UDFN 1.6x1.6x0.55 mm for Board Space Saving
- Lowest RDS(on) in 1.6x1.6 Package
- ESD Protected
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- High Side Load Switch
- PA Switch and Battery Switch
- Optimized for Power Management Applications for Portable Products, such as Cell Phones, PMP, DSC, GPS, and others

MAXIMUM RATINGS (T_{.I} = 25°C unless otherwise stated)

Parameter			Symbol	Value	Units
Drain-to-Source Voltage			V_{DSS}	-20	V
Gate-to-Source Vol	Gate-to-Source Voltage		V _{GS}	±8.0	V
Continuous Drain	Steady State	T _A = 25°C	I _D	-4.0	Α
Current (Note 1)	State	T _A = 85°C		-2.9	
	t ≤ 5 s	T _A = 25°C		-5.0	
Power Dissipa- tion (Note 1)	Steady State	T _A = 25°C	P _D	1.5	W
	t ≤ 5 s	T _A = 25°C		2.3	
Continuous Drain	Steady State	T _A = 25°C	I _D	-2.6	Α
Current (Note 2)	State	T _A = 85°C		-1.9	
Power Dissipation (Note 2) T _A = 25°C		P_{D}	0.6	W	
Pulsed Drain Current tp = 10 μs		I _{DM}	-17	Α	
Operating Junction and Storage Temperature		T _J , T _{STG}	-55 to 150	°C	
Source Current (Body Diode) (Note 2)		I _S	-0.84	Α	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		TL	260	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

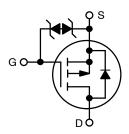
- Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
- Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm², 2 oz. Cu.



ON Semiconductor®

http://onsemi.com

MOSFET			
V _{(BR)DSS}	R _{DS(on)} MAX	I _D MAX	
	62 mΩ @ -4.5 V		
-20 V	95 mΩ @ -2.5 V	-5.0 A	
-20 V	140 mΩ @ –1.8 V	-5.07	
	230 mQ @ _1 5 V		



P-Channel MOSFET

MARKING DIAGRAM



UDFN6 CASE 517AU μCOOL™



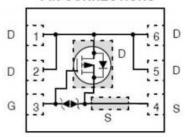
AD = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

PIN CONNECTIONS



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

1

THERMAL RESISTANCE RATINGS

Parameter		Max	Units
Junction-to-Ambient - Steady State (Note 3)		84	°C/W
Junction-to-Ambient $-t \le 5$ s (Note 3)		55	
Junction-to-Ambient - Steady State min Pad (Note 4)	$R_{\theta JA}$	200	

ELECTRICAL CHARACTERISTICS (T₁ = 25°C unless otherwise specified)

Parameter	Symbol	Test Co	ondition	Min	Тур	Max	Units
OFF CHARACTERISTICS		•		•			
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	I _D = -250 μA, ref to 25°C			-8.0		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 \text{ V},$ $T_J = 25^{\circ}\text{C}$				-1.0	μΑ
		$V_{DS} = -20 \text{ V}$	T _J = 85°C			-10	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, \	/ _{GS} = ±8.0 V			±10	μΑ
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}$	I _D = -250 μA	-0.4		-1.0	V
Negative Threshold Temp. Coefficient	V _{GS(TH)} /T _J				3.0		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = −4.5 \	V, I _D = -4.0 A		54	62	mΩ
		V _{GS} = −2.5 `	V, I _D = −2.0 A		74	95	
		V _{GS} = −1.8 '	V, I _D = -1.2 A		104	140	
		V _{GS} = −1.5 \	V, I _D = -0.5 A		137	230	
Forward Transconductance	9FS	V _{DS} = −10 \	√, I _D = −3.0 A		10		S
CHARGES, CAPACITANCES & GATE	RESISTANCE	-		-			
Input Capacitance	C _{ISS}	$V_{GS} = 0 \text{ V, f} = 1 \text{ MHz,}$ $V_{DS} = -10 \text{ V}$			950		pF
Output Capacitance	C _{OSS}				90		
Reverse Transfer Capacitance	C _{RSS}				85		
Total Gate Charge	Q _{G(TOT)}	$V_{GS} = -4.5 \text{ V}, V_{DS} = -10 \text{ V};$ $I_{D} = -3.0 \text{ A}$			12.3		nC
Threshold Gate Charge	Q _{G(TH)}				0.9		
Gate-to-Source Charge	Q _{GS}				1.6		
Gate-to-Drain Charge	Q_{GD}				3.3		
SWITCHING CHARACTERISTICS, VG	S = 4.5 V (Note 6)						
Turn-On Delay Time	t _{d(ON)}				7.9		ns
Rise Time	t _r	V_{GS} = -4.5 V, V_{DD} = -10 V, I_{D} = -3.0 A, R_{G} = 1 Ω			15.7		
Turn-Off Delay Time	t _{d(OFF)}				34.8		
Fall Time	t _f				28.5		
DRAIN-SOURCE DIODE CHARACTER	ISTICS	-		-			
Forward Diode Voltage	VSD	$V_{GS} = 0 \text{ V}, T_{J} = 25^{\circ}\text{C}$			0.74	1.2	V
		$I_{S} = -1.0 \text{ A}$ $T_{J} = 125^{\circ}\text{C}$	1	0.62			
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dis/dt = 100 A/μs, I _S = -1.0 A		1	11.8		ns
Charge Time	t _a				8.5		
Discharge Time	t _b				3.3		
Reverse Recovery Charge	Q _{RR}				6.0		nC

- Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
 Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm², 2 oz. Cu.
 Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

- 6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

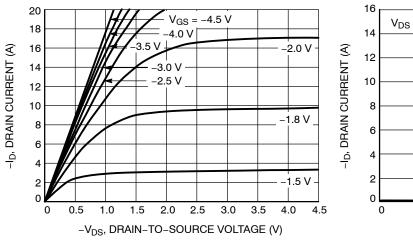
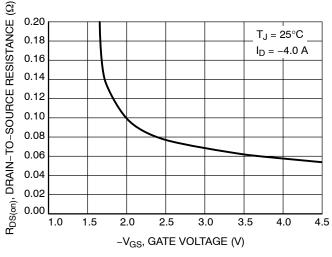


Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



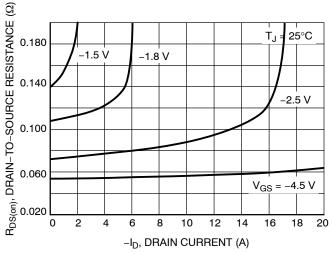
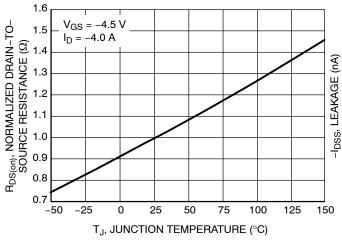


Figure 3. On-Resistance vs. Gate-to-Source Voltage

Figure 4. On-Resistance vs. Drain Current and Gate Voltage



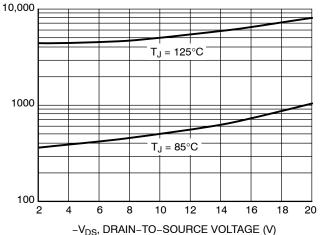
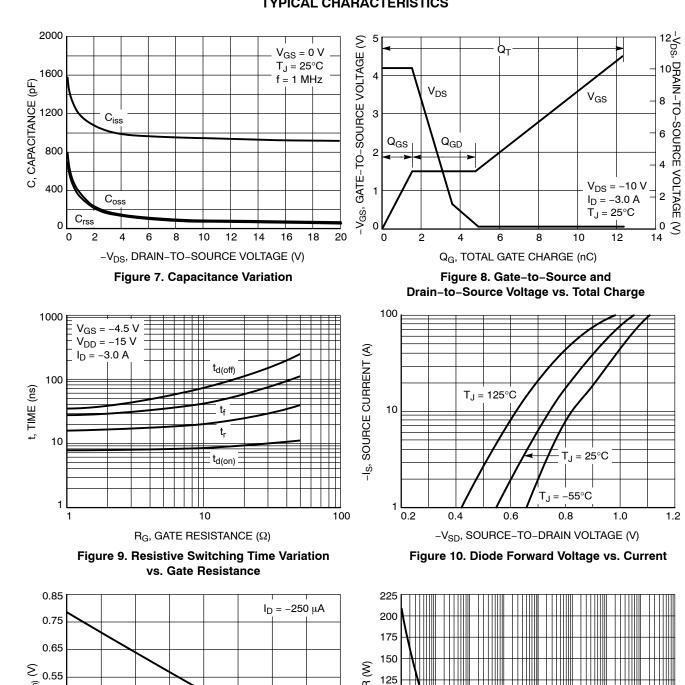


Figure 5. On–Resistance Variation with Temperature

Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS



(N 0.55 0.45 0.45 0.35 0.25

0.15

-50

-25

0

25

T_J, JUNCTION TEMPERATURE (°C) Figure 11. Threshold Voltage

50

75

100

125

150

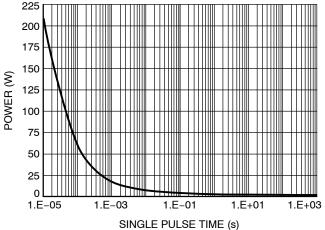


Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS

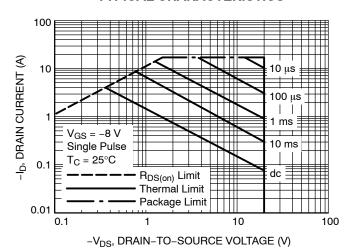


Figure 13. Maximum Rated Forward Biased Safe Operating Area

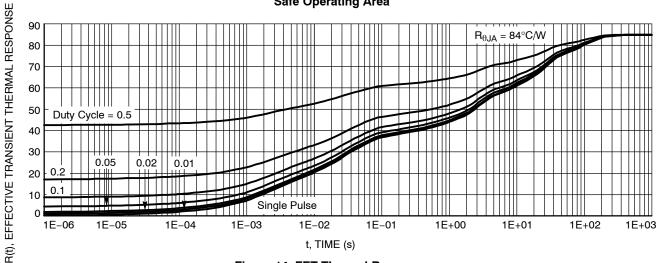


Figure 14. FET Thermal Response

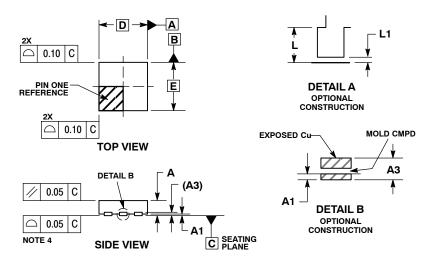
DEVICE ORDERING INFORMATION

Device	Package	Shipping [†]
NTLUS3A90PZTAG	UDFN6 (Pb-Free)	3000 / Tape & Reel
NTLUS3A90PZTBG	UDFN6 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

UDFN6 1.6x1.6, 0.5P CASE 517AU-01 ISSUE O



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0.10 C A

0.10 C A B

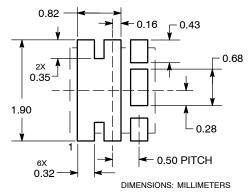
0.05 | C | NOTE 3

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM TERMINAL
- 0.30 mm FROM TERMINAL.
 COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

PAD AS WELL AS IN					
	MILLIMETERS				
DIM	MIN	MAX			
Α	0.45	0.55			
A1	0.00	0.05			
A3	0.13 REF				
b	0.20	0.30			
D	1.60 BSC				
Е	1.60 BSC				
е	0.50 BSC				
D1	0.62	0.72			
D2	0.15	0.25			
E2	0.57	0.67			
F	0.55 BSC				
G	0.25 BSC				
L	0.20	0.30			
L1		0.15			

SOLDERMASK DEFINED MOUNTING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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